

# 2SC5812

Silicon NPN Epitaxial  
VHF/UHF wide band amplifier

## HITACHI

ADE-208-1468(Z)

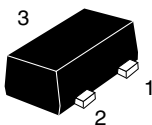
Rev.0  
Nov. 2001

### Features

- High power gain, Low noise figure at low power operation:  
 $|S_{21}|^2 = 17$  dB typ, NF = 1.0 dB typ ( $V_{CE} = 1$  V,  $I_C = 5$  mA,  $f = 900$  MHz)

### Outline

MFPAK



1. Emitter
2. Base
3. Collector

Note: Marking is "WG-".

**Absolute Maximum Ratings**

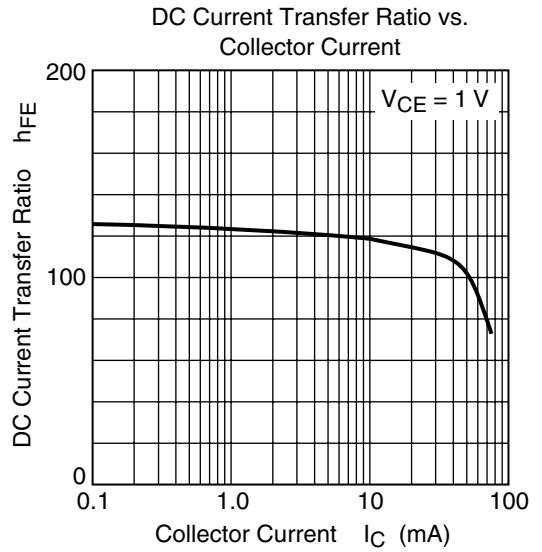
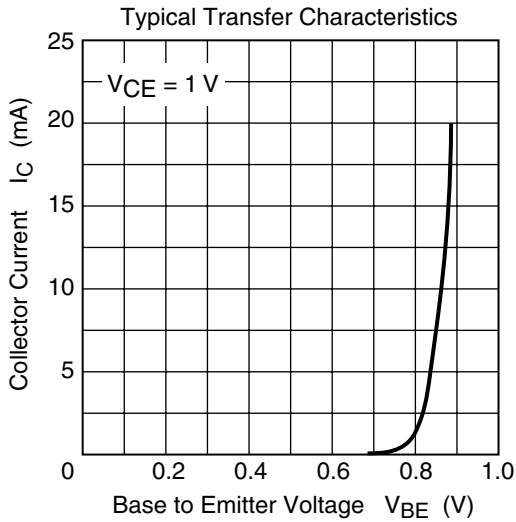
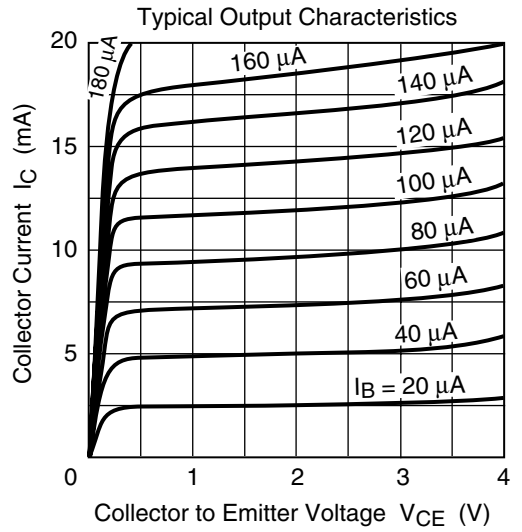
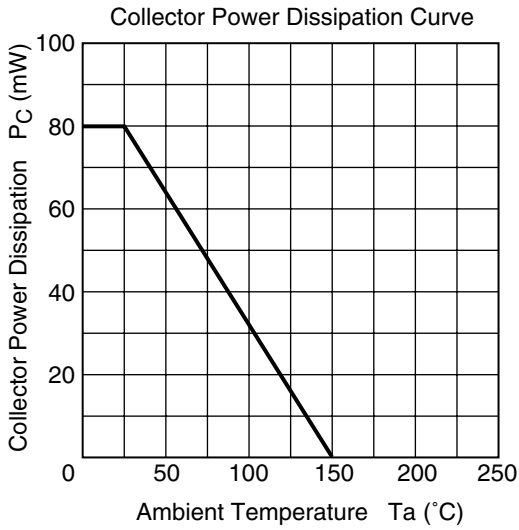
(Ta = 25°C)

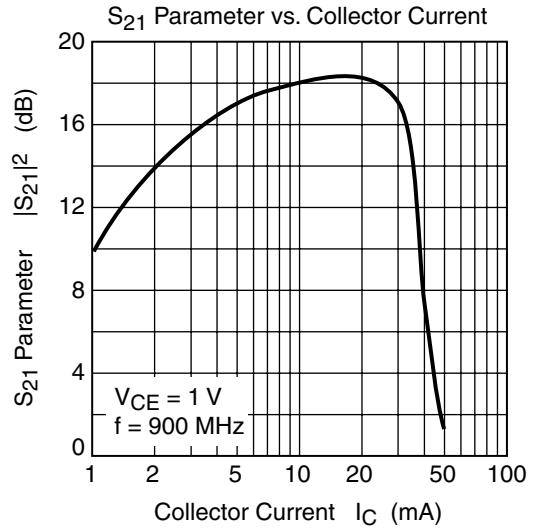
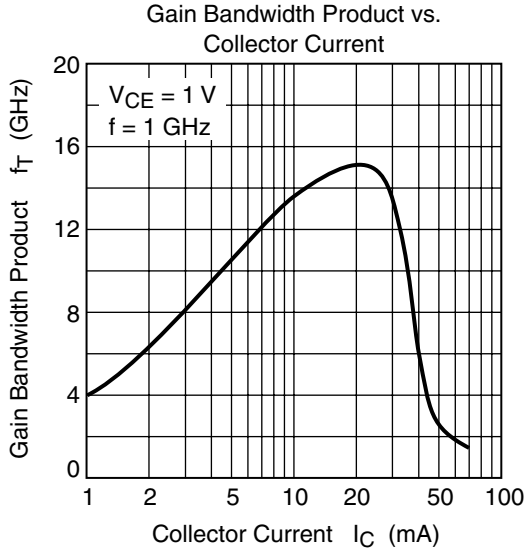
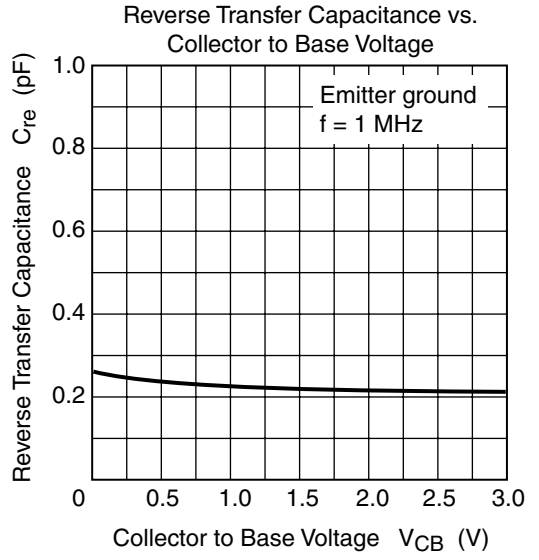
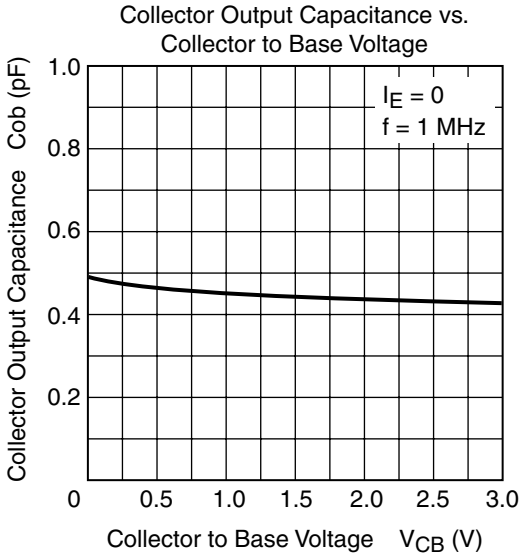
Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	15	V
Collector to emitter voltage	V <sub>CEO</sub>	4	V
Emitter to base voltage	V <sub>EBO</sub>	1.5	V
Collector current	I <sub>C</sub>	50	mA
Collector power dissipation	P <sub>C</sub>	80	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

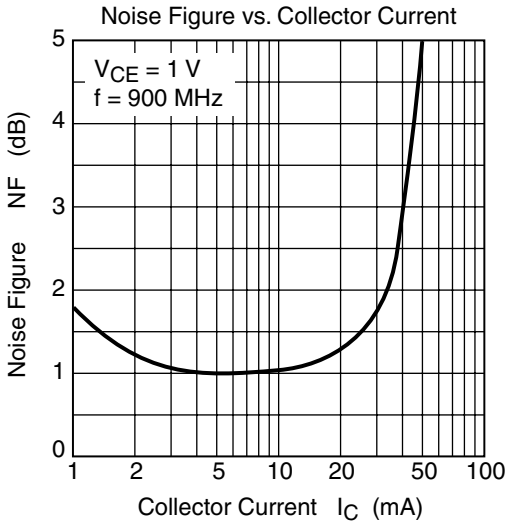
**Electrical Characteristics**

(Ta = 25°C)

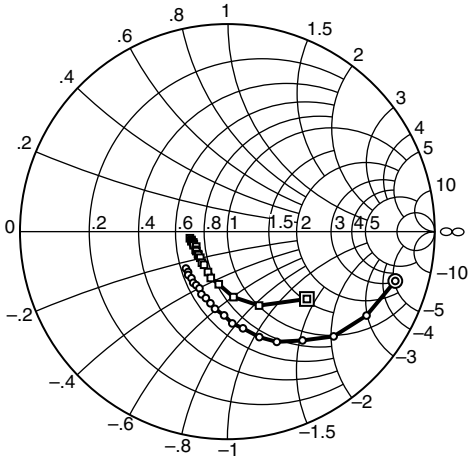
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	15	—	—	V	I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0
Collector cutoff current	I <sub>CBO</sub>	—	—	0.1	μA	V <sub>CB</sub> = 15 V, I <sub>E</sub> = 0
Collector cutoff current	I <sub>CEO</sub>	—	—	1	μA	V <sub>CE</sub> = 4 V, R <sub>BE</sub> = Infinite
Emitter cutoff current	I <sub>EBO</sub>	—	—	0.1	μA	V <sub>EB</sub> = 0.8 V, I <sub>C</sub> = 0
DC current transfer ratio	h <sub>FE</sub>	100	120	150	—	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA
Reverse transfer capacitance	C <sub>re</sub>	—	0.2	—	pF	V <sub>CE</sub> = 1 V, Emitter ground, f = 1 MHz
Collector output capacitance	C <sub>ob</sub>	—	0.4	0.7	pF	V <sub>CB</sub> = 1 V, I <sub>E</sub> = 0, f = 1 MHz
Gain bandwidth product	f <sub>T</sub> (1)	8	11	—	GHz	V <sub>CE</sub> = 1V, I <sub>C</sub> = 5 mA
Gain bandwidth product	f <sub>T</sub> (2)	—	15	—	GHz	V <sub>CE</sub> = 1V, I <sub>C</sub> = 20 mA
Forward transmission coefficient	S <sub>21</sub>   <sup>2</sup>	14	17	—	dB	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA, f = 900 MHz
Noise figure	NF	—	1.0	1.7	dB	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA, f = 900 MHz, Γ <sub>S</sub> = Γ <sub>L</sub> = 50 Ω





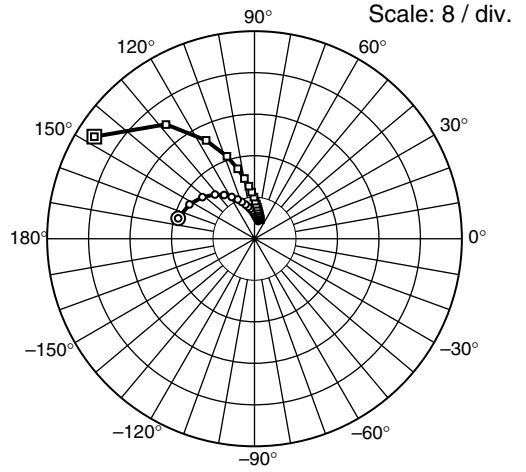


S<sub>11</sub> Parameter vs. Frequency



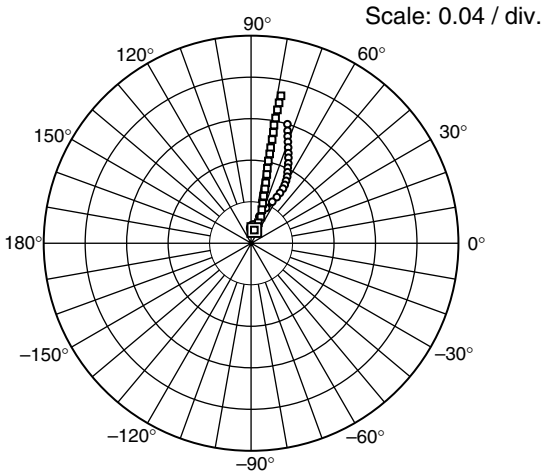
Test conditions:  $V_{CE} = 1\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz step)  
 ○—○ ( $I_C = 5\text{ mA}$ )  
 □—□ ( $I_C = 20\text{ mA}$ )

S<sub>21</sub> Parameter vs. Frequency



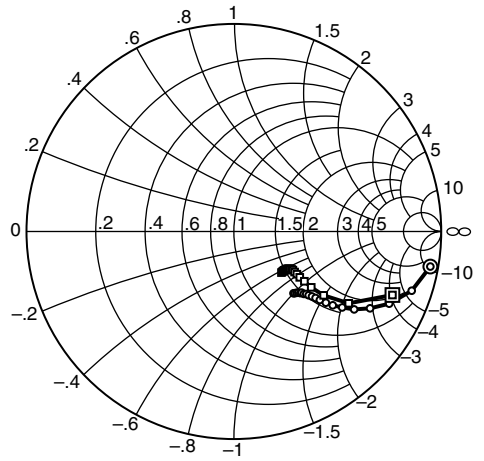
Test conditions:  $V_{CE} = 1\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz step)  
 ○—○ ( $I_C = 5\text{ mA}$ )  
 □—□ ( $I_C = 20\text{ mA}$ )

S<sub>12</sub> Parameter vs. Frequency



Test conditions:  $V_{CE} = 1\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz step)  
 ○—○ ( $I_C = 5\text{ mA}$ )  
 □—□ ( $I_C = 20\text{ mA}$ )

S<sub>22</sub> Parameter vs. Frequency



Test conditions:  $V_{CE} = 1\text{ V}$ ,  $Z_O = 50\ \Omega$   
 100 to 2000 MHz (100 MHz step)  
 ○—○ ( $I_C = 5\text{ mA}$ )  
 □—□ ( $I_C = 20\text{ mA}$ )

## S Parameter

 $(V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, Z_o = 50 \Omega)$ 

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.842	-16.3	15.23	164.9	0.015	80.2	0.963	-10.1
200	0.783	-31.7	14.17	152.2	0.027	72.9	0.904	-18.4
300	0.719	-44.6	12.84	141.4	0.037	66.8	0.826	-24.9
400	0.637	-55.4	11.41	131.8	0.045	62.9	0.754	-29.4
500	0.582	-65.9	10.25	124.8	0.051	60.8	0.691	-32.9
600	0.531	-73.2	9.16	118.6	0.056	60.1	0.638	-35.0
700	0.472	-80.9	8.22	113.1	0.061	59.7	0.595	-36.7
800	0.443	-87.0	7.49	108.9	0.065	60.0	0.561	-37.7
900	0.404	-92.3	6.80	104.6	0.069	60.7	0.530	-38.5
1000	0.377	-99.2	6.26	101.0	0.073	61.5	0.508	-39.1
1100	0.355	-103.4	5.80	98.1	0.077	62.8	0.490	-39.7
1200	0.337	-108.0	5.38	94.8	0.081	64.1	0.474	-40.4
1300	0.327	-112.6	5.04	92.4	0.085	65.0	0.461	-40.8
1400	0.305	-116.3	4.71	90.1	0.090	66.4	0.452	-41.7
1500	0.299	-120.3	4.45	87.7	0.094	67.5	0.440	-42.0
1600	0.297	-123.8	4.20	86.0	0.099	68.5	0.437	-42.8
1700	0.284	-127.7	3.98	83.6	0.104	70.0	0.428	-43.4
1800	0.282	-132.2	3.80	81.7	0.109	71.1	0.423	-44.3
1900	0.272	-134.3	3.62	79.8	0.114	72.0	0.418	-45.3
2000	0.268	-138.4	3.47	77.9	0.120	73.0	0.414	-46.0

# 2SC5812

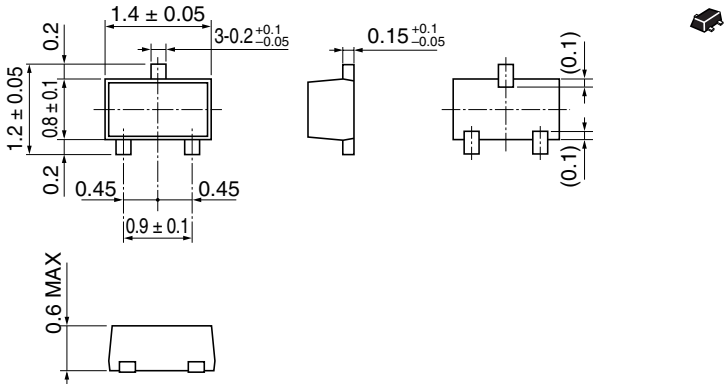
( $V_{CE} = 1\text{ V}$ ,  $I_C = 20\text{ mA}$ ,  $Z_o = 50\ \Omega$ )

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.502	-40.3	36.64	147.5	0.013	76.3	0.824	-21.8
200	0.388	-66.7	27.85	127.8	0.021	70.3	0.653	-32.0
300	0.317	-84.6	21.13	116.2	0.027	69.3	0.531	-35.4
400	0.257	-99.2	16.75	108.5	0.034	72.2	0.460	-35.8
500	0.237	-109.6	13.87	103.5	0.040	73.6	0.416	-35.2
600	0.216	-115.5	11.77	99.5	0.047	75.0	0.387	-34.8
700	0.195	-125.0	10.19	96.1	0.054	75.6	0.367	-34.1
800	0.193	-129.2	9.00	93.5	0.060	76.3	0.352	-33.7
900	0.181	-135.9	8.03	90.8	0.068	77.1	0.340	-33.2
1000	0.179	-141.0	7.26	88.8	0.074	77.7	0.333	-33.3
1100	0.178	-142.4	6.66	86.8	0.081	78.1	0.326	-33.7
1200	0.176	-147.8	6.12	84.7	0.088	78.2	0.321	-34.0
1300	0.176	-150.0	5.68	83.2	0.094	78.4	0.317	-34.5
1400	0.166	-154.2	5.32	81.7	0.102	78.5	0.314	-35.1
1500	0.175	-158.0	4.97	80.0	0.109	78.6	0.311	-36.0
1600	0.172	-159.7	4.70	78.7	0.116	79.0	0.309	-36.8
1700	0.172	-162.4	4.43	77.0	0.123	78.9	0.307	-37.6
1800	0.179	-164.9	4.21	75.7	0.131	78.8	0.305	-38.6
1900	0.177	-166.8	4.01	74.3	0.138	78.7	0.304	-39.7
2000	0.183	-169.9	3.83	72.8	0.145	78.5	0.303	-40.8



Package Dimensions

As of July, 2001  
Unit: mm



Hitachi Code	MFPAK
JEDEC	—
JEITA	—
Mass (reference value)	0.0016 g

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